East & USPB, USPT, WPID, JPO

L Number	Hits	Search Text	DB	Time stamp
1	12379	sti or (shallow with trench with isolat\$)	USPAT;	2004/09/17 20:34
			US-PGPUB	
2	104	hdcvd or hpcvd or hdcvd	USPAT;	2004/09/17 20:34
			US-PGPUB	
3	13411	Idpevd or Ipevd or Idevd	USPAT;	2004/09/17 20:34
1			US-PGPUB	
4	13614	high with cvd	USPAT;	2004/09/17 20:35
			US-PGPUB	
5	13902	low with cvd	USPAT;	2004/09/17 20:35
			US-PGPUB	
6	82726	chemical with (vapor or vapour) with deposition	USPAT;	2004/09/17 20:35
			US-PGPUB	
7	8349	high with (chemical with (vapor or vapour) with deposition)	USPAT;	2004/09/17 20:35
		·-	US-PGPUB	
8	15990	low with (chemical with (vapor or vapour) with deposition)	USPAT;	2004/09/17 20:32
			US-PGPUB	·
9	85	(sti or (shallow with trench with isolat\$)) same ((hdcvd or	USPAT;	2004/09/17 20:32
		hpcvd or hdcvd) or (high with cvd) or (high with chemical	US-PGPUB	
_		with (vapor or vapour) with deposition))) same ((ldpcvd or		
		Ipcvd or Idcvd) or (low with cvd) or (low with (chemical with		
		(vapor or vapour) with deposition)))		
10	2329739	etch\$ or patern\$ or remov\$ or \$polish\$ or cmp or grind\$ or	USPAT;	2004/09/17 20:35
		abrad\$ or planariz\$ or chemimech\$	US-PGPUB	
11	69	((sti or (shallow with trench with isolat\$)) same ((hdcvd or	USPAT;	2004/09/17 20:34
		hpcvd or hdcvd) or (high with cvd) or (high with (chemical	US-PGPUB	
		with (vapor or vapour) with deposition))) same ((Idpcvd or		
		lpcvd or ldcvd) or (low with cvd) or (low with (chemical with		
		(vapor or vapour) with deposition)))) same (etch\$ or patern\$		
		or remov\$ or \$polish\$ or cmp or grind\$ or abrad\$ or		
4.5		planariz\$ or chemimech\$)		
12	31	((sti or (shallow with trench with isolat\$)) same ((hdcvd or	USPAT;	2004/09/17 20:36
		hpcvd or hdcvd) or (high with cvd) or (high with (chemical	US-PGPUB	
		with (vapor or vapour) with deposition))) same ((ldpcvd or		
·		lpcvd or ldcvd) or (low with cvd) or (low with (chemical with		
		(vapor or vapour) with deposition)))) same (mask or		
44	2452	photomask or resist or photoresist)		
14	3153	sti or (shallow with trench with isolat\$)	JPO;	2004/09/17 20:34
15	ا ،	haloud on bound on the col	DERWENT	
15	4	hdcvd or hpcvd or hdcvd	JPO;	2004/09/17 20:34
16	050	Industrial and formed and below the	DERWENT	
16	858	ldpcvd or lpcvd or ldcvd	JPO;	2004/09/17 20:35
17	4750	high with and	DERWENT	, , , , , , , , , , , , , , , , , , , ,
17	4759	high with cvd	JPO;	2004/09/17 20:35
18	2040	law with and	DERWENT	0004/02
10	2849	low with cvd	JPO;	2004/09/17 20:35
19	10010	chamical with (vanor an arm with the second	DERWENT	
13	18010	chemical with (vapor or vapour) with deposition	JPO;	2004/09/17 20:35
20	1812	high with (chamical with (some assessment) (ii)	DERWENT	0004/00//
20	1012	high with (chemical with (vapor or vapour) with deposition)	JPO;	2004/09/17 20:35
21	1200	January 14th Annais and width Arrange and a series and width Arrange and a series a	DERWENT	
21	1300	low with (chemical with (vapor or vapour) with deposition)	JPO;	2004/09/17 20:35
22	1904620	otable ar automole or nonco de au de aliable	DERWENT	
	1804639	etch\$ or patern\$ or remov\$ or \$polish\$ or cmp or grind\$ or	JPO;	2004/09/17 20:36
23	306219	abrad\$ or planariz\$ or chemimech\$	DERWENT	0004/0047777
-~	300219	mask or photomask or resist or photoresist	JPO;	2004/09/17 20:37
24	10	(eti or (challow with trough with inslate)) and ((b.d.)d.	DERWENT	0004/00/47 == ==
	וטו	(sti or (shallow with trench with isolat\$)) and ((hdcvd or	JPO;	2004/09/17 20:37
		hpcvd or hdcvd) or (high with cvd) or (high with (chemical with (vapor or vapour) with deposition))) and ((ldpcvd or	DERWENT	
1		with (vapor or vapour) with deposition ()) and ((idbcvd or	1	
	i	Inoud or Idoud) or (low with out) or (low with /abanical with		l
	.	lpcvd or Idcvd) or (low with cvd) or (low with (chemical with (vapor or vapour) with deposition)))		*

25	8	((sti or (shallow with trench with isolat\$)) and ((hdcvd or	JPO;	2004/09/17 20:37
23		hpcvd or hdcvd) or (high with cvd) or (high with (chemical	DERWENT	200 11 20.07
		with (vapor or vapour) with deposition))) and ((ldpcvd or		
		lpcvd or ldcvd) or (low with cvd) or (low with (chemical with		
		(vapor or vapour) with deposition)))) and ((etch\$ or patern\$		
		or remov\$ or \$polish\$ or cmp or grind\$ or abrad\$ or		
		planariz\$ or chemimech\$) or (mask or photomask or resist or		
		photoresist))	IDO.	2004/00/47 20:20
26	10	((sti or (shallow with trench with isolat\$)) and ((hdcvd or	JPO; DERWENT	2004/09/17 20:38
		hpcvd or hdcvd) or (high with cvd) or (high with (chemical	DERWEINI	:
		with (vapor or vapour) with deposition))) and ((Idpcvd or		
		Ipcvd or Idcvd) or (low with cvd) or (low with (chemical with (vapor or vapour) with deposition)))) or (((sti or (shallow with		
		trench with isolat\$)) and ((hdcvd or hpcvd or hdcvd) or (high		
		with cvd) or (high with (chemical with (vapor or vapour) with		
		deposition))) and ((Idpcvd or Ipcvd or Idcvd) or (Iow with cvd)		
		or (low with (chemical with (vapor or vapour) with		
		deposition)))) and ((etch\$ or patern\$ or remov\$ or \$polish\$ or		
		cmp or grind\$ or abrad\$ or planariz\$ or chemimech\$) or		
		(mask or photomask or resist or photoresist)))		
13	85	((sti or (shallow with trench with isolat\$)) same ((hdcvd or	USPAT;	2004/09/17 20:45
		hpcvd or hdcvd) or (high with cvd) or (high with (chemical	US-PGPUB	
	ļ	with (vapor or vapour) with deposition))) same ((Idpcvd or		
		lpcvd or ldcvd) or (low with cvd) or (low with (chemical with		
		(vapor or vapour) with deposition)))) or (((sti or (shallow with		·
		trench with isolat\$)) same ((hdcvd or hpcvd or hdcvd) or		
		(high with cvd) or (high with (chemical with (vapor or vapour)		
		with deposition))) same ((Idpcvd or Ipcvd or Idcvd) or (Iow	:	
		with cvd) or (low with (chemical with (vapor or vapour) with		
		deposition)))) same (etch\$ or patern\$ or remov\$ or \$polish\$		
		or cmp or grind\$ or abrad\$ or planariz\$ or chemimech\$)) or (((sti or (shallow with trench with isolat\$)) same ((hdcvd or		
		hpevd or hdevd) or (high with evd) or (high with (chemical		
		with (vapor or vapour) with deposition))) same ((Idpcvd or	* '	
		Ipcvd or Idcvd) or (low with cvd) or (low with (chemical with		
		(vapor or vapour) with deposition)))) same (mask or		
		photomask or resist or photoresist))		
27	25	(((sti or (shallow with trench with isolat\$)) same ((hdcvd or	USPAT;	2004/09/17 20:46
		hpcvd or hdcvd) or (high with cvd) or (high with (chemical	US-PGPUB	
		with (vapor or vapour) with deposition))) same ((ldpcvd or		:
		Ipcvd or Idcvd) or (low with cvd) or (low with (chemical with		
		(vapor or vapour) with deposition)))) or (((sti or (shallow with		
		trench with isolat\$)) same ((hdcvd or hpcvd or hdcvd) or		
		(high with cvd) or (high with (chemical with (vapor or vapour)		
		with deposition))) same ((Idpcvd or Ipcvd or Idcvd) or (Iow		
		with cvd) or (low with (chemical with (vapor or vapour) with		
		deposition)))) same (etch\$ or patern\$ or remov\$ or \$polish\$		
		or cmp or grind\$ or abrad\$ or planariz\$ or chemimech\$)) or (((sti or (shallow with trench with isolat\$)) same ((hdcvd or		
		hpcvd or hdcvd) or (high with cvd) or (high with (chemical	,	
		with (vapor or vapour) with deposition))) same ((Idpcvd or		
		Ipcvd or Idcvd) or (low with cvd) or (low with (chemical with		
		(vapor or vapour) with deposition)))) same (mask or		
		photomask or resist or photoresist))) and (sti or (shallow with		
		trench\$ with isolat\$)).ti.		

(((sti or (shallow with trench with isolat\$)) same ((hdcvd or hpcvd or hdcvd) or (high with (chemical with (vapor or vapour) with deposition))) same ((ldpcvd or lpcvd or ldcvd) or (low with cvd) or (low with (chemical with (vapor or vapour) with deposition)))) or (((sti or (shallow with trench with isolat\$)) same ((hdcvd or hpcvd or hdcvd) or (high with cvd) or (high with (chemical with (vapor or vapour) with deposition)))) same ((ldpcvd or lpcvd or ldcvd) or (low with cvd) or (low with cvd) or (low with (chemical with (vapor or vapour) with deposition)))) same ((ldpcvd or lpcvd or ldcvd) or (((sti or (shallow with trench with isolat\$)) same ((hdcvd or hpcvd or hdcvd) or (high with cvd) or (high with (chemical with (vapor or vapour) with deposition)))) same ((ldpcvd or lpcvd or ldcvd) or (low with cvd) or (low with (chemical with (vapor or vapour) with deposition)))) same ((ldpcvd or hpcvd or hdcvd) or (high with cvd) or (high with (vapor or vapour) with deposition))) same ((hdcvd or hpcvd or hdcvd) or (high with cvd) or (high with (vapor or vapour) with deposition)))) same ((ldpcvd or lpcvd or ldcvd) or (low with cvd) or (high with cvd) or (low with (chemical with (vapor or vapour) with deposition)))) same ((ldpcvd or lpcvd or ldcvd) or (low with cvd) or (high with	•		
with (chemical with (vapor or vapour) with deposition))) same ((Idpcvd or Ipcvd or Idcvd) or (Iow with cvd) or (Iow with (chemical with (vapor or vapour) with deposition)))) same (etch\$ or patern\$ or remov\$ or \$polish\$ or cmp or grind\$ or abrad\$ or planariz\$ or chemimech\$)) or (((sti or (shallow with trench with isolat\$)) same ((hdcvd or hpcvd or hdcvd) or (high with cvd) or (high with (chemical with (vapor or vapour) with deposition))) same ((Idpcvd or Ipcvd or Idcvd) or (Iow	28 60	hpcvd or hdcvd) or (high with cvd) or (high with (chemical with (vapor or vapour) with deposition))) same ((Idpcvd or Ipcvd or Idcvd) or (Iow with cvd) or (Iow with (chemical with (vapor or vapour) with deposition)))) or (((sti or (shallow with trench with isolat\$)) same ((Idpcvd or hpcvd or hdcvd) or (high with cvd) or (high with (chemical with (vapor or vapour) with deposition)))) same ((Idpcvd or Ipcvd or Idcvd) or (Iow with cvd) or (Iow with (chemical with (vapor or vapour) with deposition)))) same (etch\$ or patern\$ or remov\$ or \$polish\$ or cmp or grind\$ or abrad\$ or planariz\$ or chemimech\$)) or (((sti or (shallow with trench with isolat\$)) same ((Idpcvd or Ipcvd or Idcvd) or (high with cvd) or (high with (chemical with (vapor or vapour) with deposition)))) same ((Idpcvd or Ipcvd or Idcvd) or (Iow with cvd) or (Iow with (chemical with (vapor or vapour) with deposition)))) same ((Idpcvd or Ipcvd or Idcvd) or (Iow with cvd) or (Iow with (chemical with (vapor or vapour) with deposition)))) same ((Idpcvd or Ipcvd or Idcvd) or (Iow with cvd) or (Iow with (chemical with (vapor or vapour) with deposition)))) same ((Idpcvd or Ipcvd or Idcvd) or (Iow with (chemical with (vapor or vapour) with deposition)))) same ((Idpcvd or Ipcvd or Idcvd) or (high with cvd) or (high with cvd) or (high with cvd) or (low with (chemical with (vapor or vapour) with deposition)))) same ((Idpcvd or Ipcvd or Idcvd) or (Iow with (chemical with (vapor or vapour) with deposition)))) same ((Idpcvd or Ipcvd or Idcvd) or (Iow with cvd) or (Iow with (chemical with (vapor or vapour) with deposition)))) same ((Idpcvd or Ipcvd or Idcvd) or (Iow with cvd) or (Iow with (chemical with (vapor or vapour) with deposition)))) same ((Idpcvd or Ipcvd or Idcvd) or (Iow with cvd) or (Iow with (chemical with (vapor or vapour) with deposition)))) same (Idpcvd or Ipcvd or Idcvd) or (Iow with cvd) or (Iow with (chemical with (vapor or vapour) with Incomposition)))) same (Idpcvd or Ipcvd or Idcvd) or Incomposition))))	2004/09/17 20:46



			· · · · · · · · · · · · · · · · · · ·
	FILE	'CAPLUS	5' ENTERED AT 19:57:59 ON 17 SEP 2004
L1		3250 S	STI OR (SHALLOW WITH TRENCH? WITH ISOLAT?)
L2		596 S	STIS
L3		3858 S	LPCVD OR LCVD OR LOW(W)PRESSURE(W)CVD
L4		646 S	LOW (W) PRESSURE (W) CHEMICAL (W) VAPOR (W) DEPOSITION
L5		52 S	HPCVD OR HCVD OR HIGH(W)PRESSURE(W)CVD
L6		7 S	HIGH (W) PRESSURE (W) CHEMICAL (W) VAPOR (W) DEPOSITION
L7		26 S	(L1 OR L2) AND (L3 OR L4)
$\Gamma8$		1 S	L7 AND (L5 OR L6)
L 9		25 S	L7 NOT L8
L10		9 S	L9 AND HIGH AND PRESSURE
L11		16 S	L9 NOT L10
1.12		0 S	I.11 AND HP

(FILE 'HOME' ENTERED AT 20:18:05 ON 17 SEP 2004)

FILE 'CAPLUS' ENTERED AT 20:18:13 ON 17 SEP 2004

L1	0	S	HDCVD
L2	2	S	LDCVD
L3	79	S	HDPCVD
L4	3236	S	STI OR SHALLOW (W) TRENCH? (W) ISOLAT?
L5.	28	S	L3 AND L4
L6	3858	S	LPCVD OR LCVD OR LOW(W) PRES? (W) CVD
L7	741	S	LOW (W) PRES? (W) CHEMICAL (W) VAPOR (W) DEPOSIT?
L8	3	S	L5 AND (L6 OR L7)